

14P5 Rec'd PCT/PTO 28 SEP 2006

10/594846

Atty. Dkt. 28953.2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Makoto IWAI et al

Serial No. (new)

Based on PCT/JP2005/006692

Int'l Filing Date: March 30, 2005

For: GALLIUM NITRIDE SINGLE CRYSTAL GROWING METHOD
AND GALLIUM NITRIDE SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Customer Window
U.S. Patent & Trademark Office
Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached Form PTO-1449. A copy of the foreign references listed on Form PTO-1449 is attached.

Refs. AE-AG are cited in the International Search Report, copy attached. References AP, AC and AD are discussed at page 1 of the specification. U.S. Patent No. 6,398,867 (Ref. AB) corresponds to Japanese Patent Publication 2003-511326 (AE).

The above information is presented so that the Patent and Trademark Office may, in the first instance, determine any materiality thereof to the claimed invention. See 37 C.F.R. 1.104(a) and 1.106(b) concerning the PTO duty to consider and use any such information. It is respectfully

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requested that the information be expressly considered during the prosecution of this application, and that these references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Respectfully submitted,

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| Form PTO-1449 (Modified) | U.S. Department of Commerce Patent and Trademark Office | Attorney's Docket No. 28953.2004 | Application No. New - unassigned |
| Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b)) | | Applicant Makoto IWA et al | |
| | | Filing Date Herewith | Group Art Unit |

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U.S. Patent Documents

| Examiner Initial | Desig. ID | Patent Number | Issue Date | Patentee | Class | Subclass | Filing Date If Appropriate |
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| | AA | 6,949,140 | 9/2005 | Sarayama et al | 117 | 81 | |
| | AB | 6,398,867 | 6/2002 | D'Evelyn et al | 117 | 11 | |

Foreign Patent Documents or Published Foreign Patent Applications

| Examiner Initial | Desig. ID | Document Number | Publn. Date | Country or Patent Office | Class | Subclass | Translation | |
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| | | | | | | | Yes | No |
| | AC | 2002-293696 | 10/2002 | Japan | | | Abstract | |
| | AD | 2003-292400 | 10/2003 | Japan | | | Abstract | |
| | AE | 2003-511326 | 3/2003 | Japan | | | X | |
| | AF | 2005-8444 | 1/2005 | Japan | | | Abstract | |
| | AG | WO2004/013385 | 6/2003 | WIPO | | | Abstract | |
| | AH | WO01/024921 | 9/2000 | WIPO | | | | |
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Other Documents (include Author, Title, Date, and Place of Publication)

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| | AP | Kawamura, F. et al, "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique," Jpn. J. Appl. Phys., Vol. 42 (2003), pp. L4-L6 |
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| | AR | |
| | AS | |
| | AT | |

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|--|-----------------|
| Examiner Signature | Date Considered |
| EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |